



# RF Power Field Effect Transistors

## N-Channel Enhancement-Mode Lateral MOSFETs

Designed for N-CDMA base station applications with frequencies from 869 to 960 MHz. Suitable for multicarrier amplifier applications.

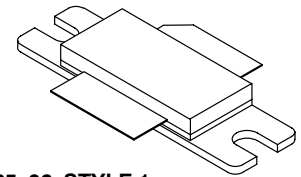
- Typical Single-Carrier N-CDMA Performance @ 880 MHz:  $V_{DD} = 28$  Volts,  $I_{DQ} = 1500$  mA,  $P_{out} = 33$  Watts Avg., IS-95 CDMA (Pilot, Sync, Paging, Traffic Codes 8 Through 13). Channel Bandwidth = 1.2288 MHz. PAR = 9.8 dB @ 0.01% Probability on CCDF.  
Power Gain — 19.7 dB  
Drain Efficiency — 28.4%  
ACPR @ 750 kHz Offset — -46.8 dBc in 30 kHz Bandwidth
- Capable of Handling 10:1 VSWR, @ 28 Vdc, 880 MHz, 150 Watts CW Output Power

### Features

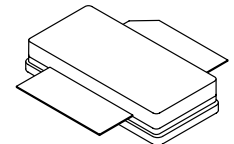
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Qualified Up to a Maximum of 32  $V_{DD}$  Operation
- Integrated ESD Protection
- Lower Thermal Resistance Package
- Low Gold Plating Thickness on Leads, 40 $\mu$  Nominal.
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

**MRF5S9150HR3**  
**MRF5S9150HSR3**

**880 MHz, 33 W AVG., 28 V**  
**SINGLE N-CDMA**  
**LATERAL N-CHANNEL**  
**RF POWER MOSFETs**



**CASE 465-06, STYLE 1**  
**NI-780**  
**MRF5S9150HR3**



**CASE 465A-06, STYLE 1**  
**NI-780S**  
**MRF5S9150HSR3**

**Table 1. Maximum Ratings**

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	-0.5, +68	Vdc
Gate-Source Voltage	$V_{GS}$	-0.5, +15	Vdc
Storage Temperature Range	$T_{stg}$	- 65 to +150	$^{\circ}C$
Case Operating Temperature	$T_C$	150	$^{\circ}C$
Operating Junction Temperature	$T_J$	200	$^{\circ}C$

**Table 2. Thermal Characteristics**

Characteristic	Symbol	Value (1)	Unit
Thermal Resistance, Junction to Case Case Temperature 80 $^{\circ}C$ , 150 W CW Case Temperature 76 $^{\circ}C$ , 33 W CW	$R_{\theta JC}$	0.34 0.34	$^{\circ}C/W$

**Table 3. ESD Protection Characteristics**

Test Methodology	Class
Human Body Model (per JESD22-A114)	1C (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	III (Minimum)

1. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>.  
Select Documentation/Application Notes - AN1955.

**Table 4. Electrical Characteristics** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>Off Characteristics</b>					
Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 68\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ )	$I_{DSS}$	—	—	10	$\mu\text{Adc}$
Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 28\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ )	$I_{DSS}$	—	—	1	$\mu\text{Adc}$
Gate-Source Leakage Current ( $V_{GS} = 5\text{ Vdc}$ , $V_{DS} = 0\text{ Vdc}$ )	$I_{GSS}$	—	—	500	$\text{nAdc}$

**On Characteristics**

Gate Threshold Voltage ( $V_{DS} = 10\text{ Vdc}$ , $I_D = 600\ \mu\text{Adc}$ )	$V_{GS(th)}$	2	3	4	Vdc
Gate Quiescent Voltage ( $V_{DS} = 28\text{ Vdc}$ , $I_D = 1500\ \text{mAdc}$ , Measured in Functional Test)	$V_{GS(Q)}$	3	4	5	Vdc
Drain-Source On-Voltage ( $V_{GS} = 10\text{ Vdc}$ , $I_D = 3.15\ \text{Adc}$ )	$V_{DS(on)}$	0.1	0.2	0.3	Vdc

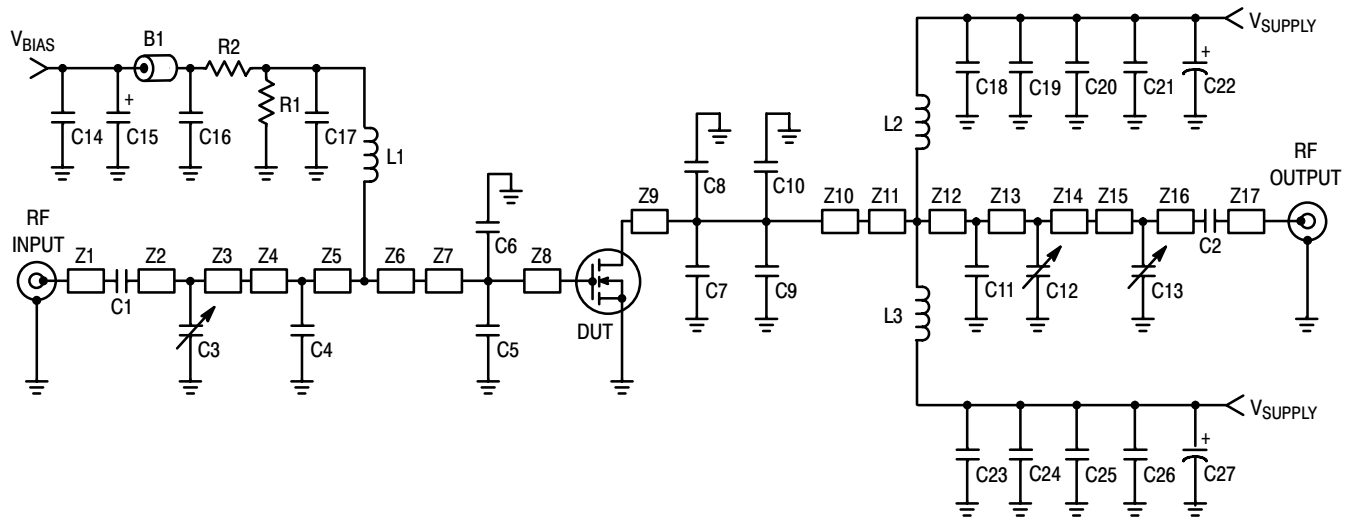
**Dynamic Characteristics** (1)

Reverse Transfer Capacitance ( $V_{DS} = 28\text{ Vdc} \pm 30\ \text{mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$ )	$C_{rss}$	—	3.1	—	pF
Output Capacitance ( $V_{DS} = 28\text{ Vdc} \pm 30\ \text{mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$ )	$C_{oss}$	—	91.5	—	pF

**Functional Tests** (In Freescale Test Fixture, 50 ohm system)  $V_{DD} = 28\text{ Vdc}$ ,  $I_{DQ} = 1500\ \text{mA}$ ,  $P_{out} = 33\ \text{W Avg. N-CDMA}$ ,  $f = 880\ \text{MHz}$ , Single-Carrier N-CDMA, 1.2288 MHz Channel Bandwidth Single Carrier. ACPR measured in 30 kHz Channel Bandwidth @  $\pm 750\ \text{kHz}$  Offset. PAR = 9.8 dB @ 0.01% Probability on CCDF.

Power Gain	$G_{ps}$	18.5	19.7	21.5	dB
Drain Efficiency	$\eta_D$	26.5	28.4	—	%
Adjacent Channel Power Ratio	ACPR	—	-46.8	-45	dBc
Input Return Loss	IRL	—	-20	-9	dB

1. Part internally input matched.



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Z1	0.416" x 0.080" Microstrip	Z10	0.105" x 0.630" Microstrip
Z2	0.851" x 0.080" Microstrip	Z11	0.200" x 0.630" x 0.220" Taper
Z3, Z17	0.410" x 0.080" Microstrip	Z12	0.236" x 0.220" Microstrip
Z4	0.055" x 0.220" Microstrip	Z13	0.195" x 0.220" Microstrip
Z5	0.434" x 0.220" Microstrip	Z14	0.059" x 0.220" Microstrip
Z6	0.200" x 0.220" x 0.630" Taper	Z15	0.989" x 0.080" Microstrip
Z7	0.077" x 0.630" Microstrip	Z16	0.284" x 0.080" Microstrip
Z8	0.221" x 0.630" Microstrip	PCB	Arlon GX-0300-55-22, 0.030", $\epsilon_r = 2.55$
Z9	0.193" x 0.630" Microstrip		

**Figure 1. MRF5S9150HR3(HSR3) Test Circuit Schematic**

**Table 5. MRF5S9150HR3(HSR3) Test Circuit Component Designations and Values**

Part	Description	Part Number	Manufacturer
B1	Small Ferrite Bead	2743019447	Fair Rite
C1, C2, C17	47 pF Chip Capacitors	100B470JP500X	ATC
C3, C12	0.8-8.0 pF Variable Capacitors, Gigatrim	27291SL	Johanson
C4	13 pF Chip Capacitor	100B130JP500X	ATC
C5, C6	15 pF Chip Capacitors	100B150JP500X	ATC
C7, C8	12 pF Chip Capacitors	100B120JP500X	ATC
C9, C10	4.3 pF Chip Capacitors	100B4R3JP500X	ATC
C11	8.2 pF Chip Capacitor	100B8R2JP500X	ATC
C13	0.6-4.5 pF Variable Capacitor, Gigatrim	27271SL	Johanson
C14	22 pF Chip Capacitor	100B220JP500X	ATC
C15	1 $\mu$ F, 50 V Tantalum Capacitor	T491C105K0J0AS	Kemite
C16	20K pF Chip Capacitor	CDR353P203AK0S	Kemite
C18, C23	180 pF Chip Capacitors	100B181JP500X	ATC
C19, C20, C21, C24, C25, C26	10 $\mu$ F, 50 V Chip Capacitors (2220)	GRM55DR61H106KA88B	Murata
C22, C27	470 $\mu$ F, 63 V Electrolytic Capacitors	KME63VB471M12x25LL	United Chemi-Con
L1, L2, L3	12.5 nH Inductors	A04T	Coilcraft
R1	180 k $\Omega$ , 1/4 W Chip Resistor		
R2	10 $\Omega$ , 1/4 W Chip Resistor		

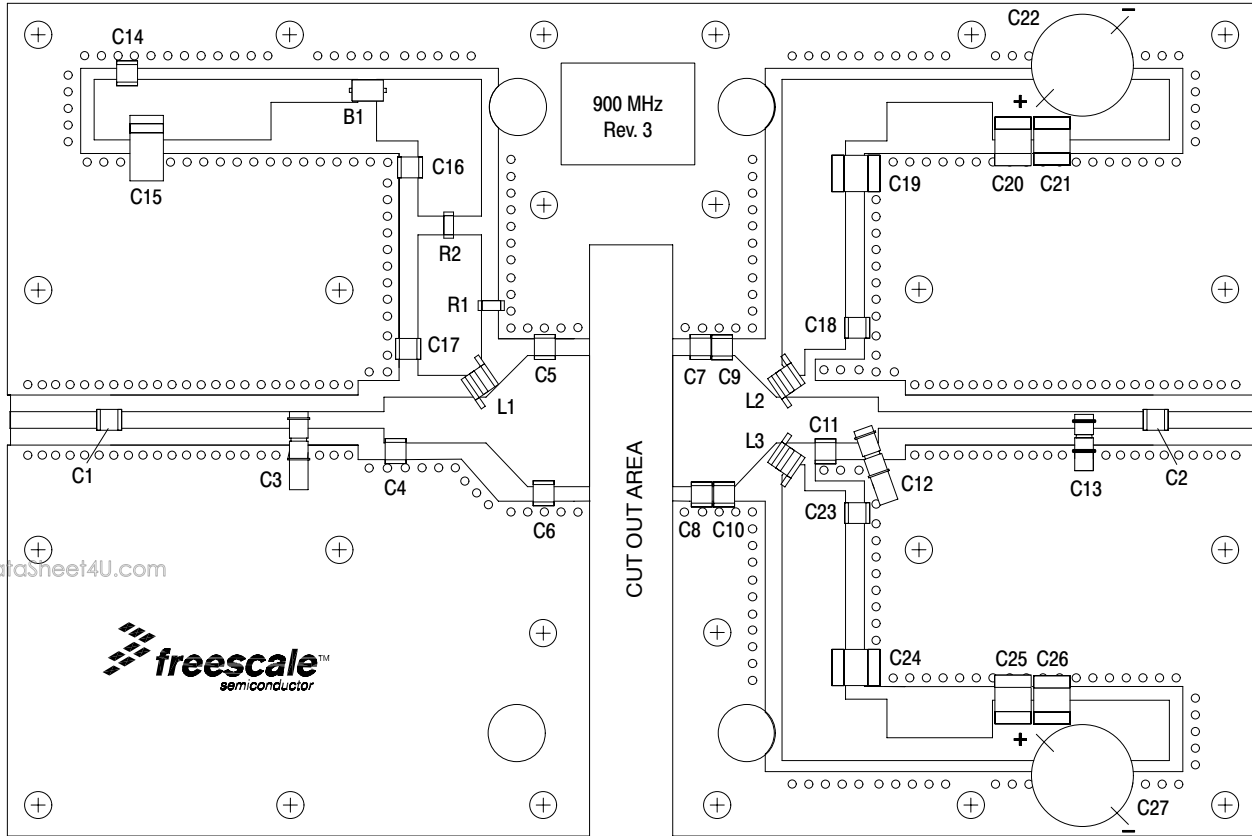


Figure 2. MRF5S9150HR3(HSR3) Test Circuit Component Layout

## TYPICAL CHARACTERISTICS

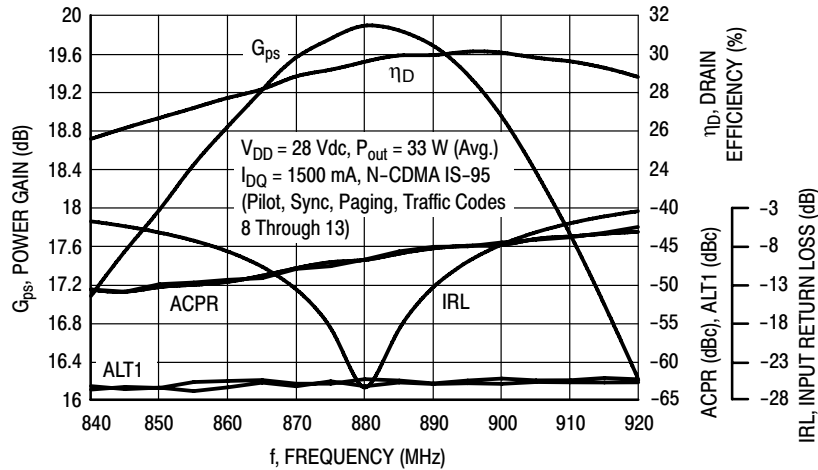


Figure 3. Single-Carrier N-CDMA Broadband Performance @  $P_{out} = 33$  Watts Avg.

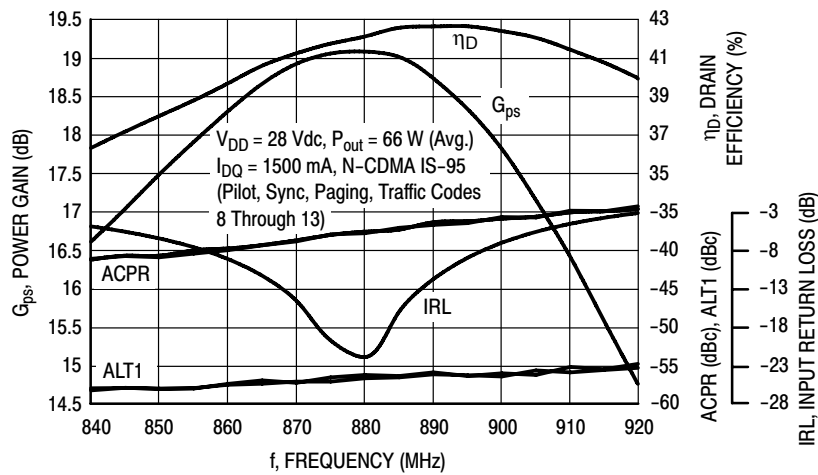


Figure 4. Single-Carrier N-CDMA Broadband Performance @  $P_{out} = 66$  Watts Avg.

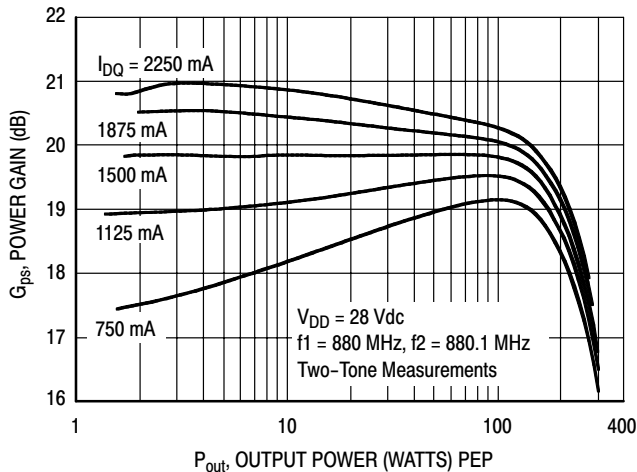


Figure 5. Two-Tone Power Gain versus Output Power

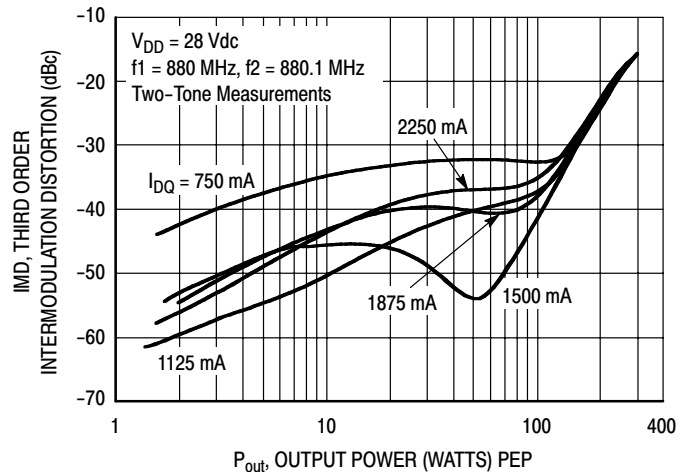
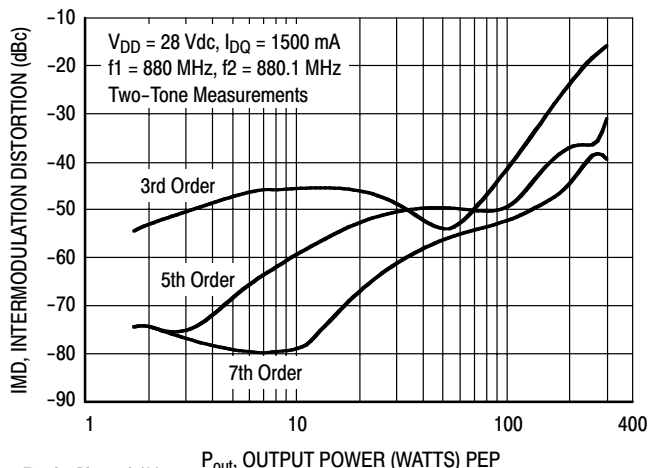
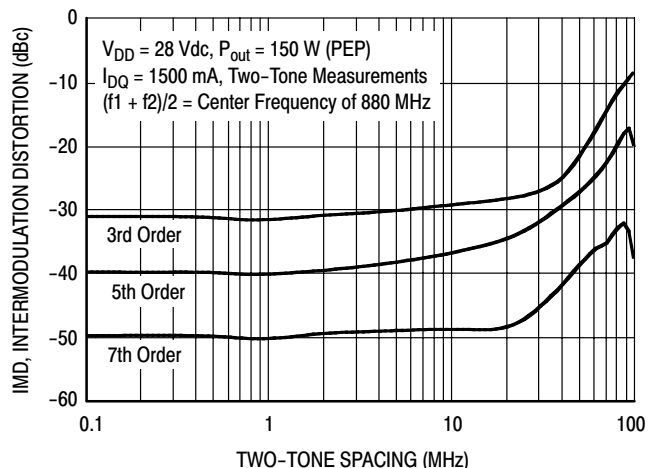


Figure 6. Third Order Intermodulation Distortion versus Output Power

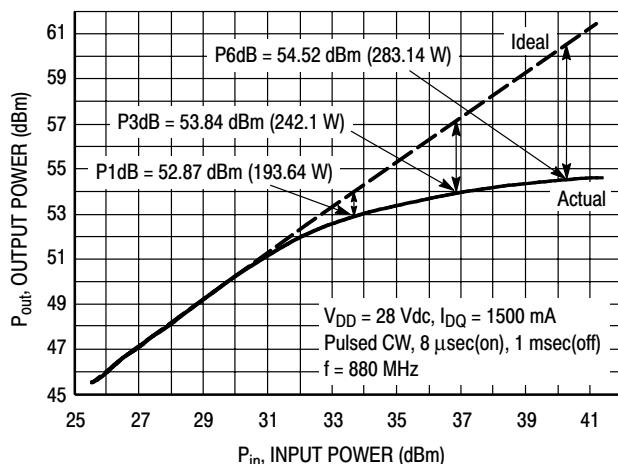
## TYPICAL CHARACTERISTICS



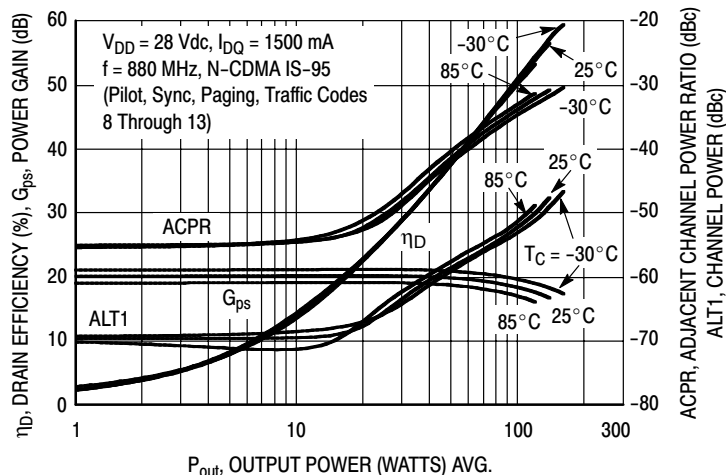
**Figure 7. Intermodulation Distortion Products versus Output Power**



**Figure 8. Intermodulation Distortion Products versus Tone Spacing**

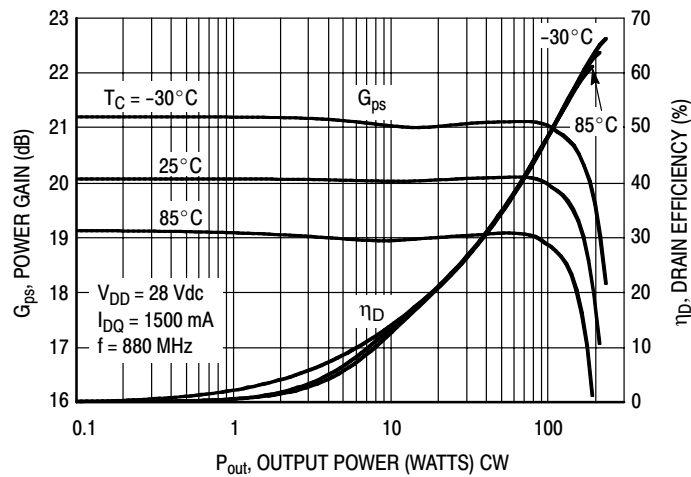


**Figure 9. Pulse CW Output Power versus Input Power**

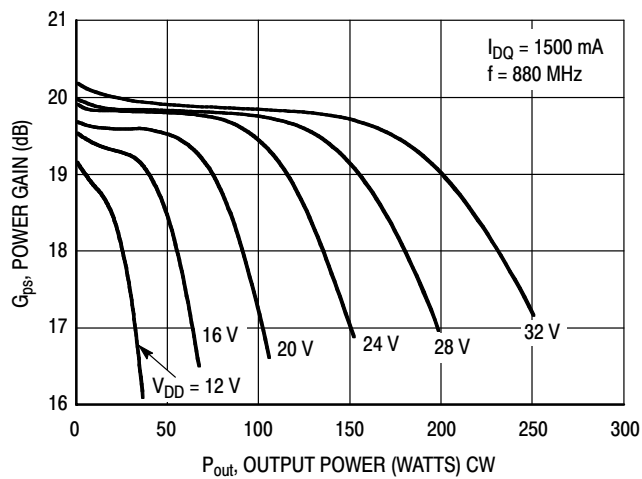


**Figure 10. Single-Carrier N-CDMA ACPR, ALT1, Power Gain and Drain Efficiency versus Output Power**

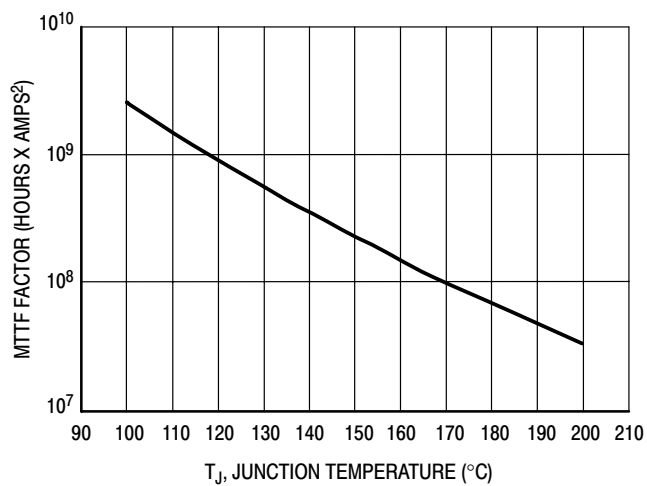
## TYPICAL CHARACTERISTICS



**Figure 11. Power Gain and Drain Efficiency versus CW Output Power**



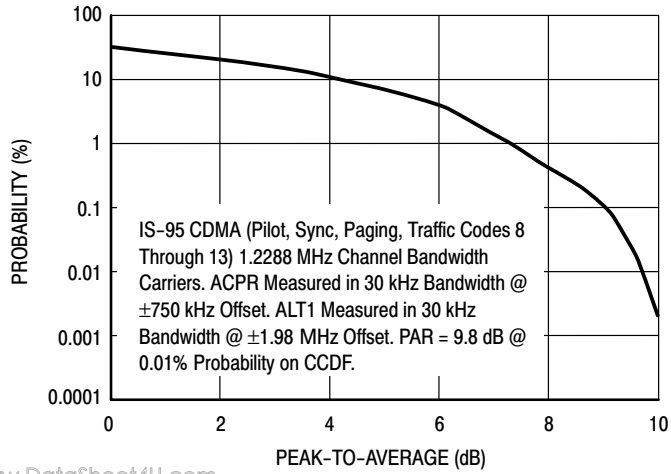
**Figure 12. Power Gain versus Output Power**



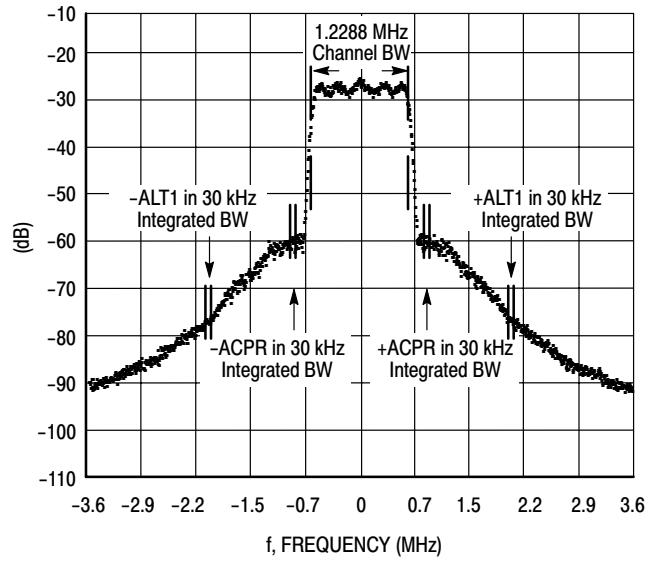
This above graph displays calculated MTTF in hours x ampere<sup>2</sup> drain current. Life tests at elevated temperatures have correlated to better than  $\pm 10\%$  of the theoretical prediction for metal failure. Divide MTTF factor by  $I_D^2$  for MTTF in a particular application.

**Figure 13. MTTF Factor versus Junction Temperature**

## N-CDMA TEST SIGNAL

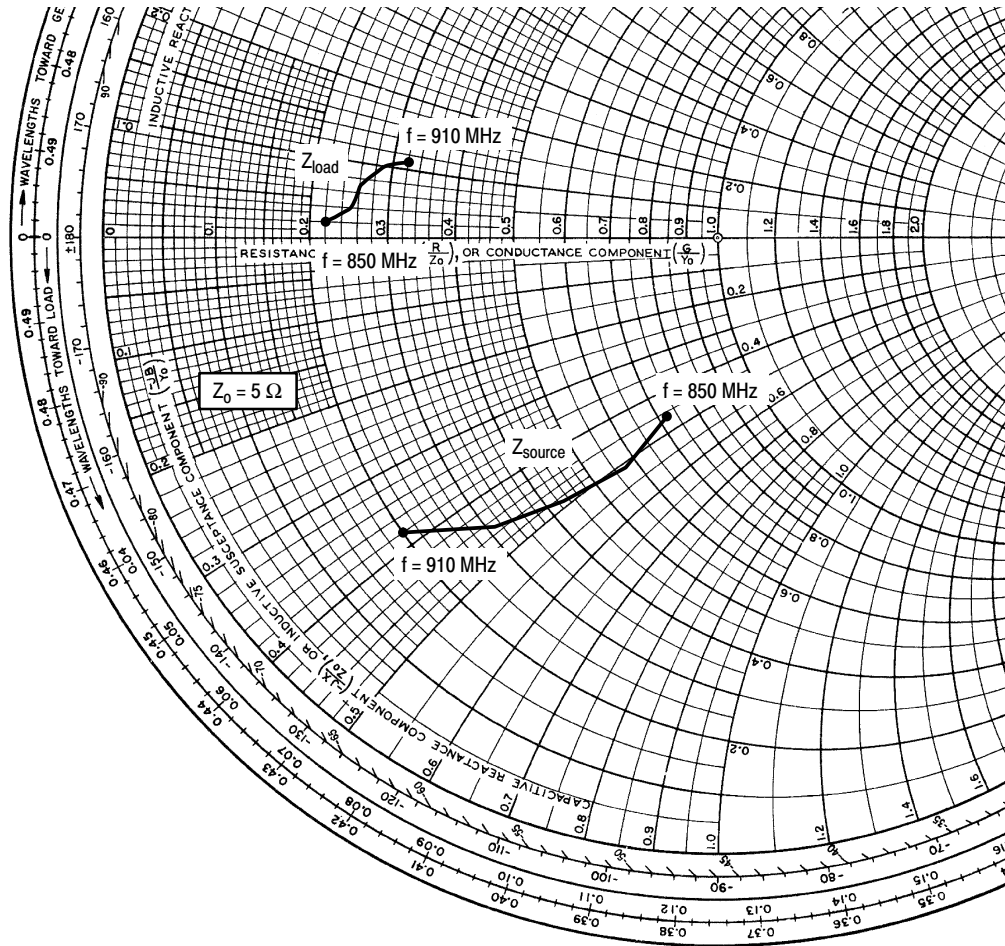


**Figure 14. Single-Carrier CCDF N-CDMA**



**Figure 15. Single-Carrier N-CDMA Spectrum**





$V_{DD} = 28 \text{ Vdc}$ ,  $I_{DQ} = 1500 \text{ mA}$ ,  $P_{out} = 33 \text{ W Avg.}$

f MHz	$Z_{source}$ $\Omega$	$Z_{load}$ $\Omega$
850	$3.61 - j2.30$	$1.12 + j0.09$
865	$2.85 - j2.54$	$1.24 + j0.22$
880	$2.13 - j2.47$	$1.31 + j0.36$
895	$1.53 - j2.27$	$1.46 + j0.48$
910	$1.02 - j1.90$	$1.61 + j0.53$

$Z_{source}$  = Test circuit impedance as measured from gate to ground.

$Z_{load}$  = Test circuit impedance as measured from drain to ground.

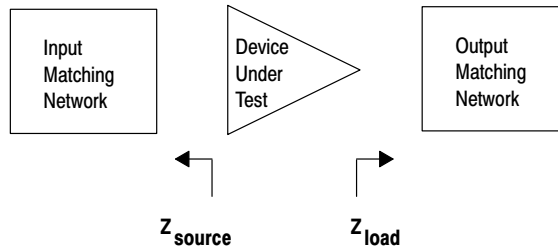
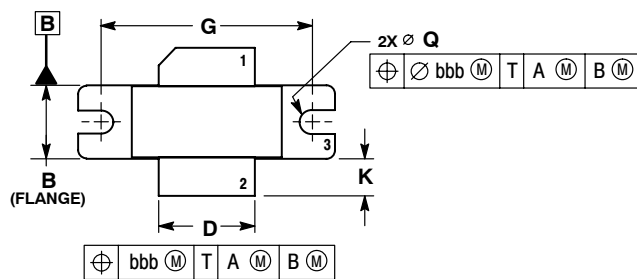


Figure 16. Series Equivalent Source and Load Impedance

# NOTES

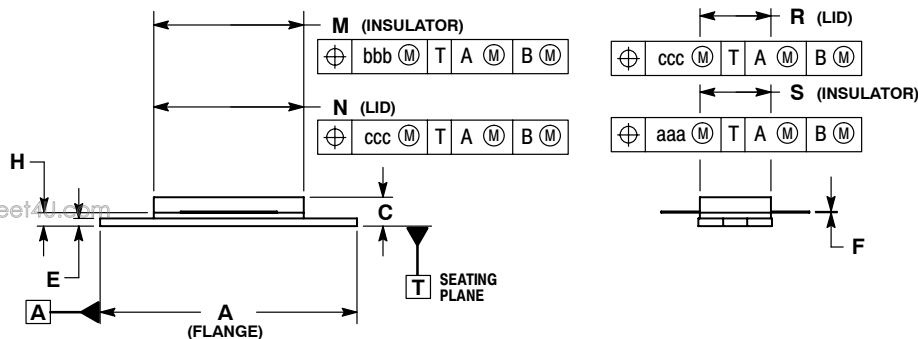
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## PACKAGE DIMENSIONS



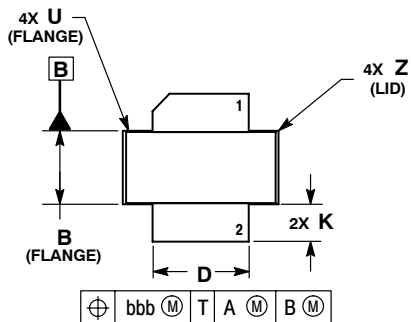
- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
  2. CONTROLLING DIMENSION: INCH.
  3. DELETED
  4. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.335	1.345	33.91	34.16
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
G	1.100	BSC	27.94	BSC
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.66	19.96
N	0.772	0.788	19.60	20.00
Q	Ø.118	Ø.138	Ø3.00	Ø3.51
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
aaa	0.005	REF	0.127	REF
bbb	0.010	REF	0.254	REF
ccc	0.015	REF	0.381	REF



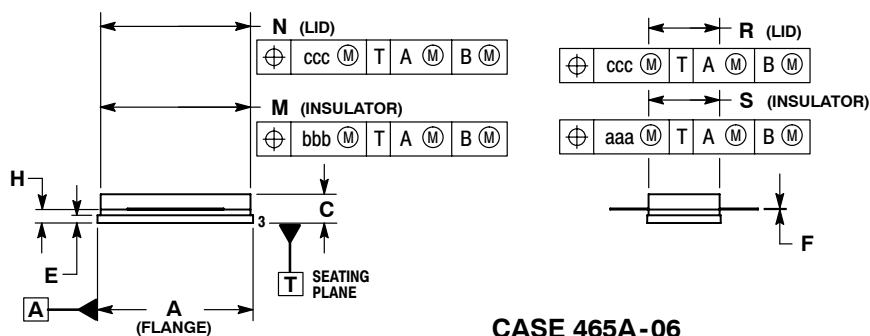
**CASE 465-06  
ISSUE G  
NI-780  
MRF5S9150HR3**

- STYLE 1:  
PIN 1. DRAIN  
2. GATE  
3. SOURCE



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
  2. CONTROLLING DIMENSION: INCH.
  3. DELETED
  4. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.805	0.815	20.45	20.70
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.61	20.02
N	0.772	0.788	19.61	20.02
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
U	---	0.040	---	1.02
Z	---	0.030	---	0.76
aaa	0.005	REF	0.127	REF
bbb	0.010	REF	0.254	REF
ccc	0.015	REF	0.381	REF



**CASE 465A-06  
ISSUE H  
NI-780S  
MRF5S9150HSR3**

- STYLE 1:  
PIN 1. DRAIN  
2. GATE  
5. SOURCE

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